

Growth of Individual Carbon Nanotubes with Precise location

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Abstract

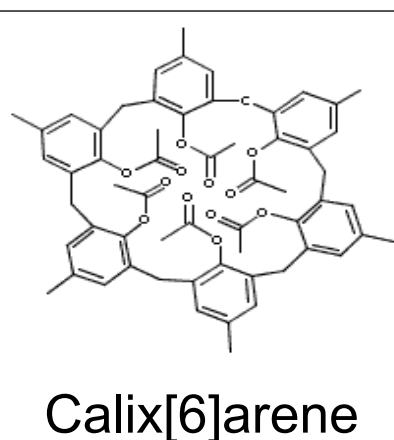
Electronic devices based on individual single-walled carbon nanotubes (SWCNTs) remain at the prototype level because of the limited reliability of the growth processes and the absence of control over electrical properties and positioning of the obtained nanotubes. To improve the location and narrow the electronic property distribution of the SWCNTs, we have developed a method based on a negative-tone e-beam resist doped with Co. At the end of the process, individual particles with a diameter of $1.2 \pm 0.2 \text{ nm}$ are localized within an area of 80 nm^2 . From these particles, high-quality SWCNTs are grown by a Chemical Vapor Deposition (CVD) with high yield from ethanol. The process is being integrated into the fabrication process of the nano electro-mechanical system (NEMS) developed by our partners at ETHZ.

Catalyst formation process

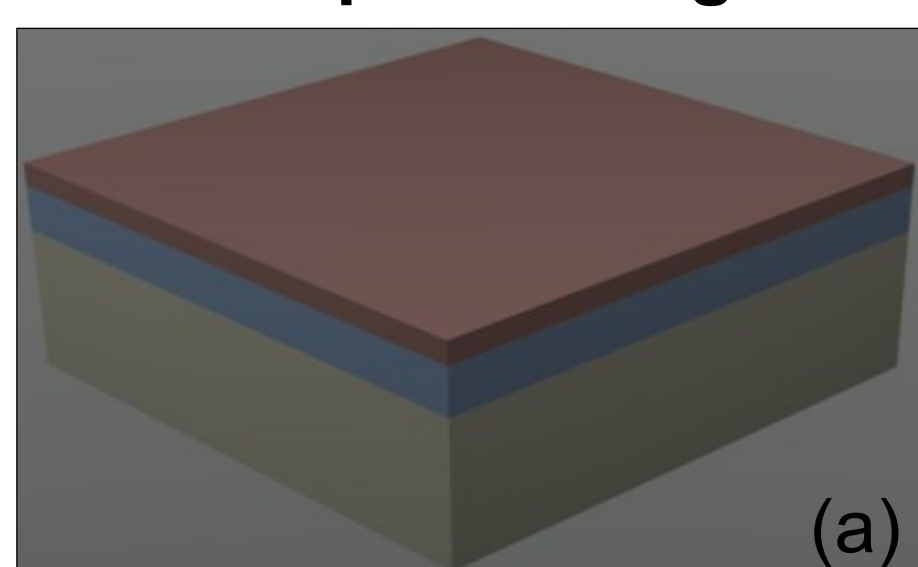
1: Resist preparation

Resist solution:

- 0.75 wt% calix[6]arene
- $\text{Co}(\text{Acac})_3$
- Monochlorobenzene

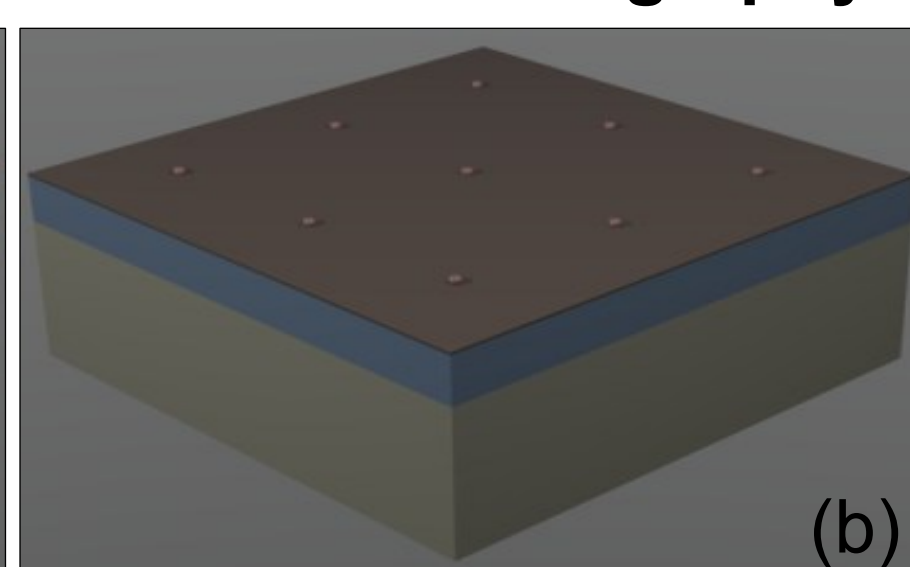


2: Spin coating



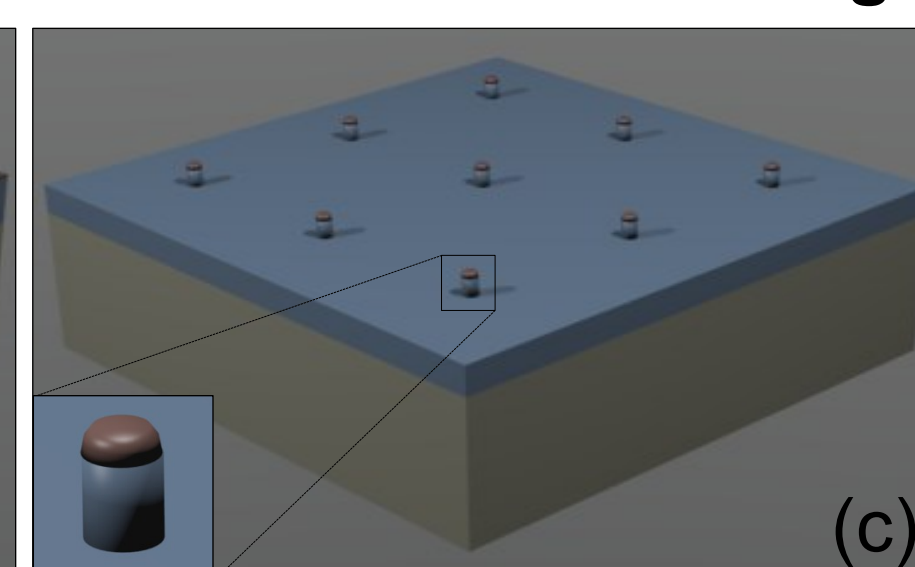
Co doped e-beam resist
 SiO_2
Si

3: E-beam Lithography

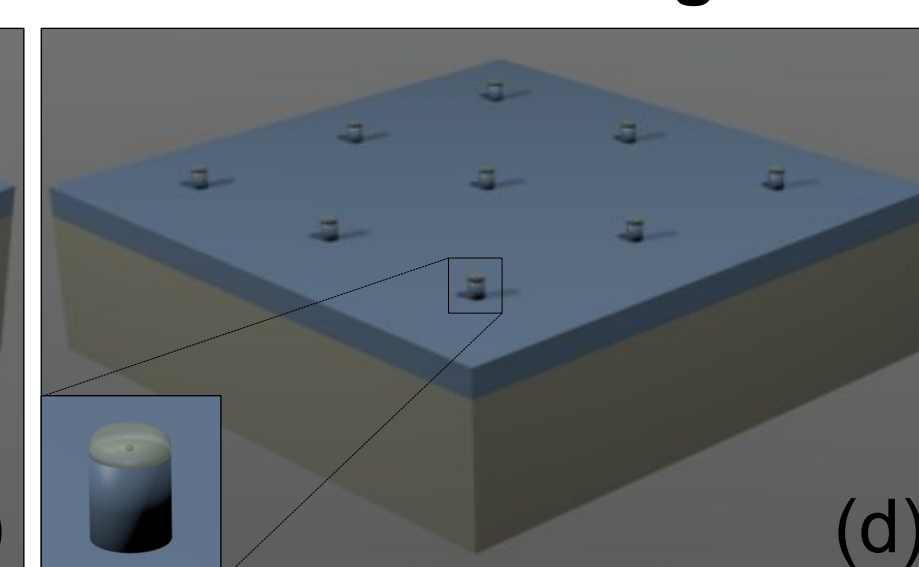


Contaminations

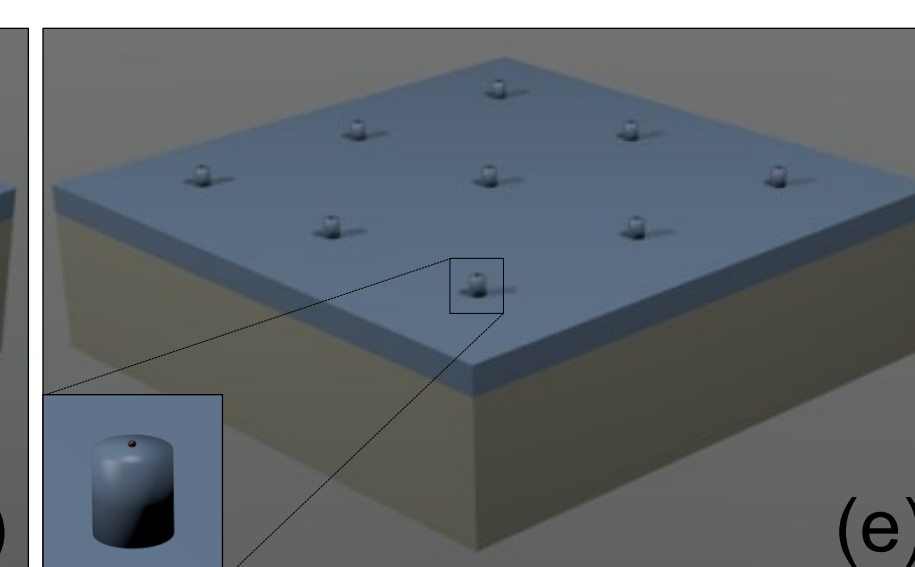
4: Reactive Ion Etching



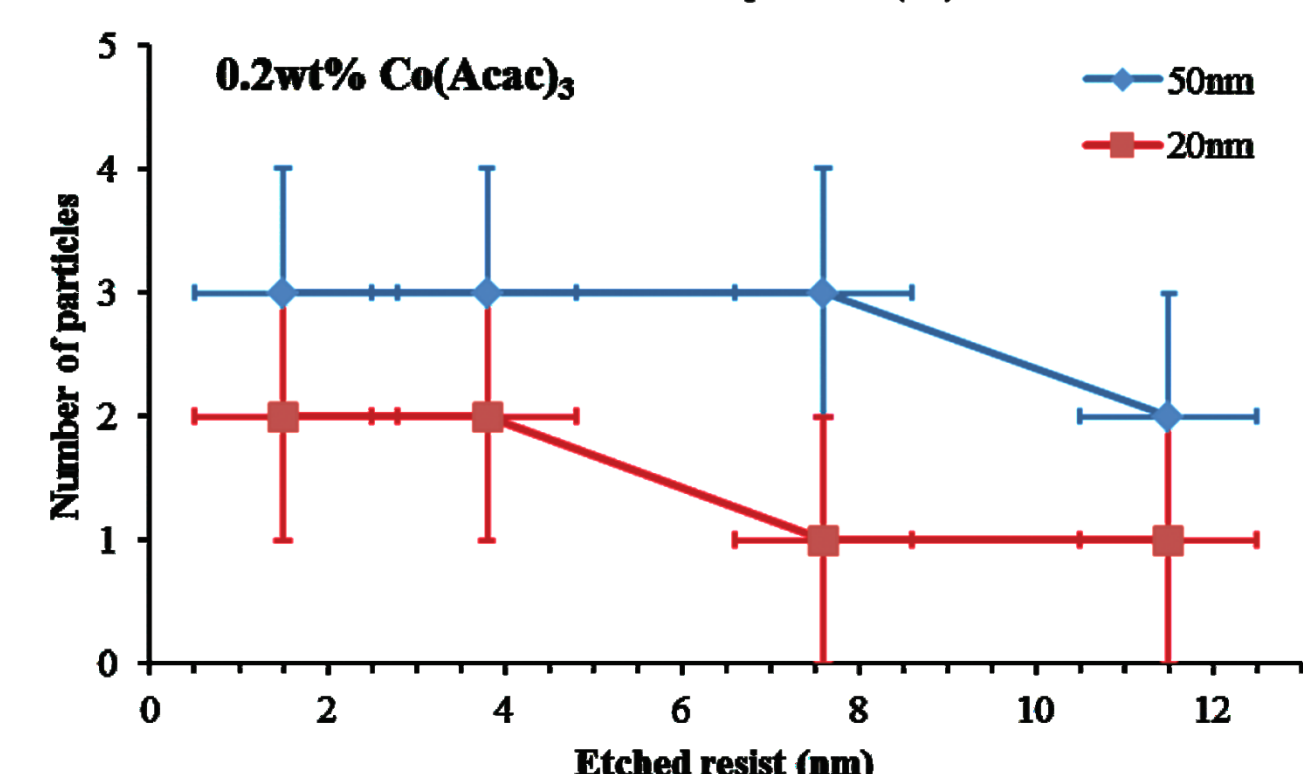
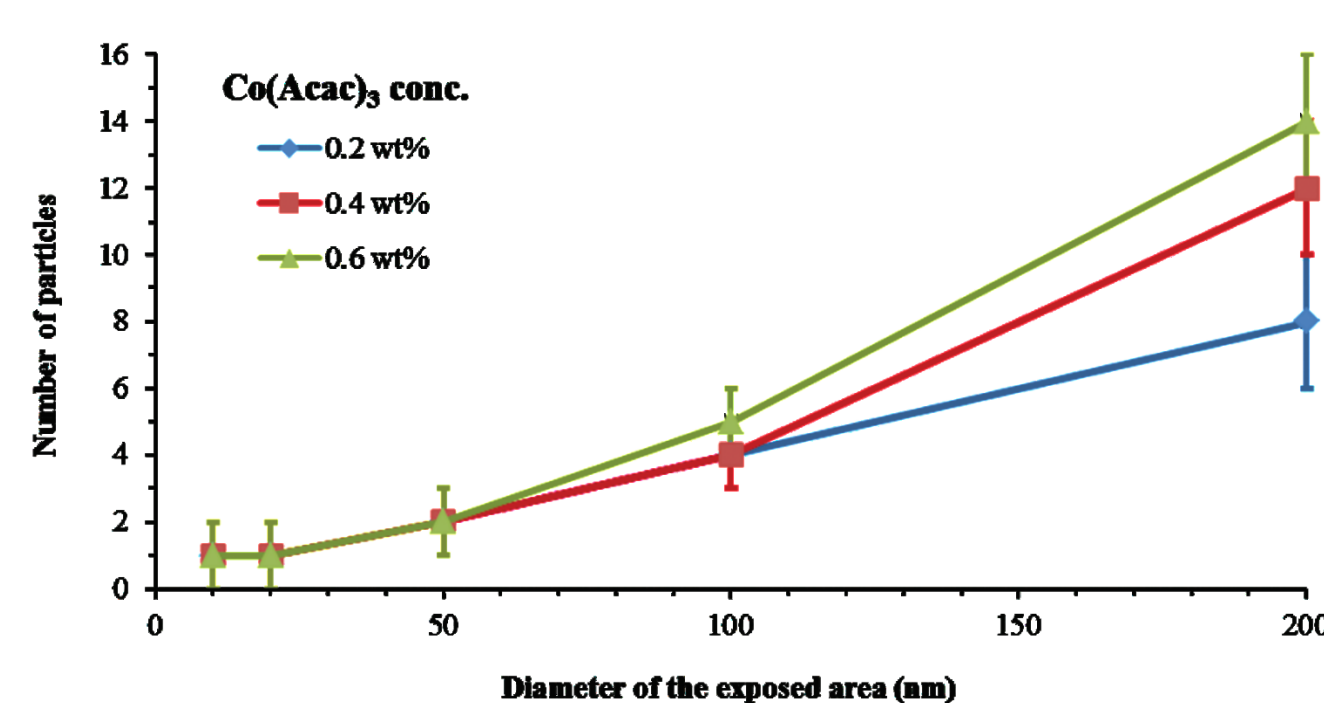
5: Annealing



6: Oxidation

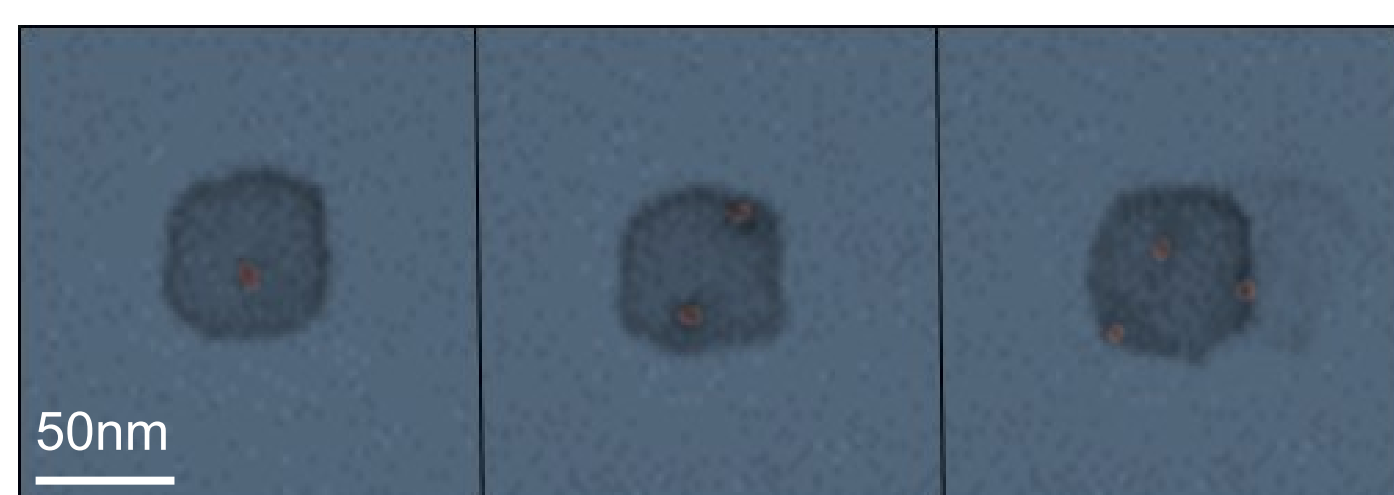
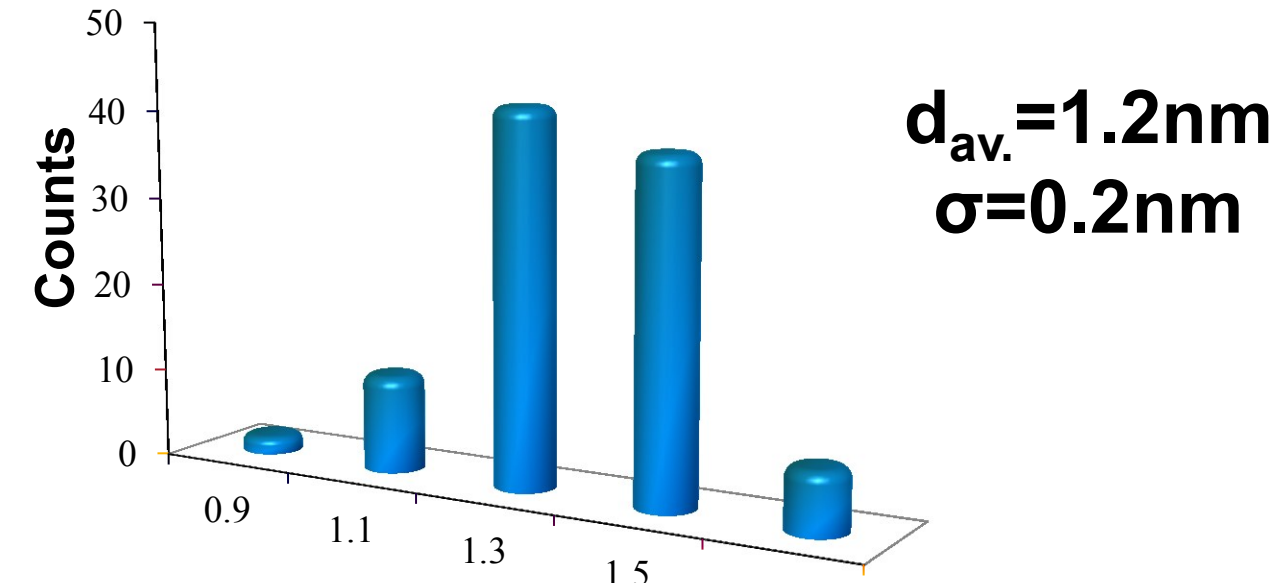


Characterization of the Catalyst Particles



AFM analysis

Particle diameter(nm)

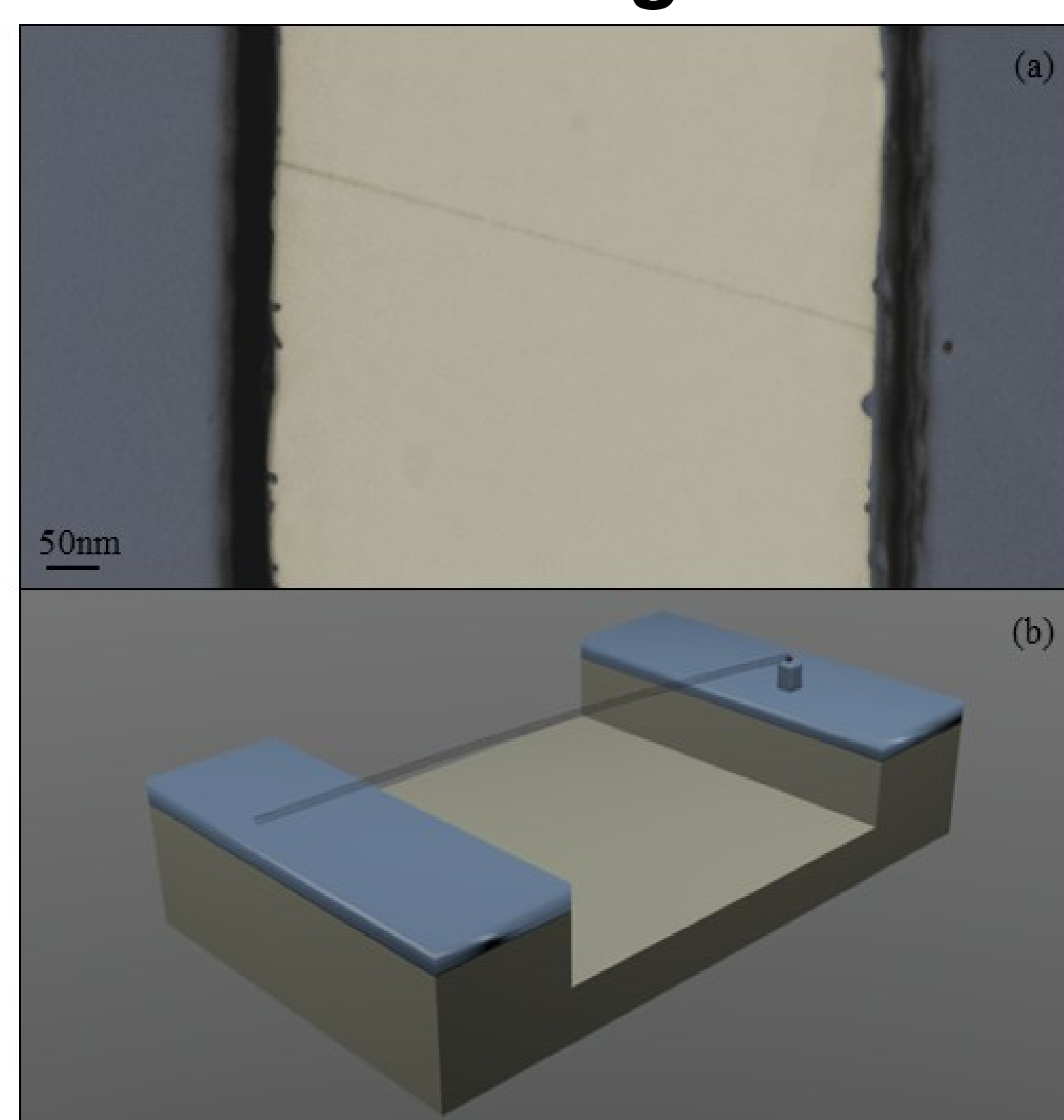


Colored HRSEM micrographs of three pillars with a diameter of 50nm. The number of particles varies according to the RIE time and the Co concentration in the calix[6]arene resist.

HIGHLIGHTS:

- Localisation of one particle within an area of 80 nm^2
- Narrow Particle Diameter Distribution

Growth of Single-walled carbon nanotubes

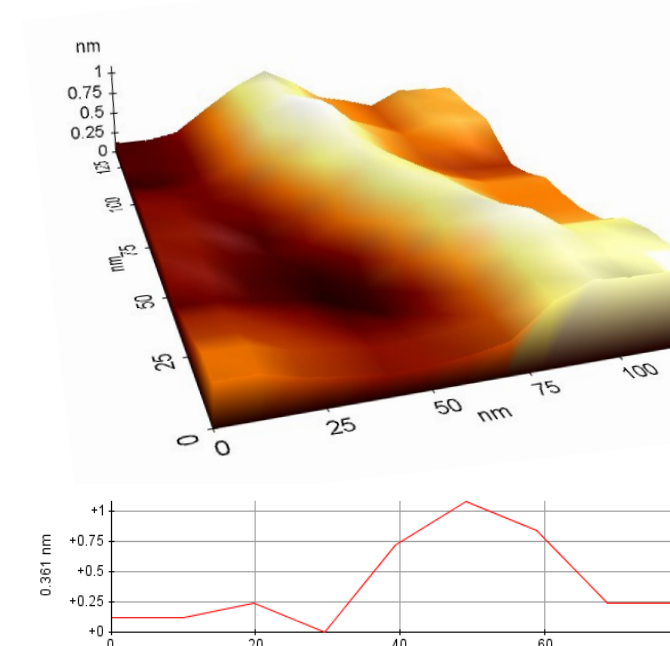
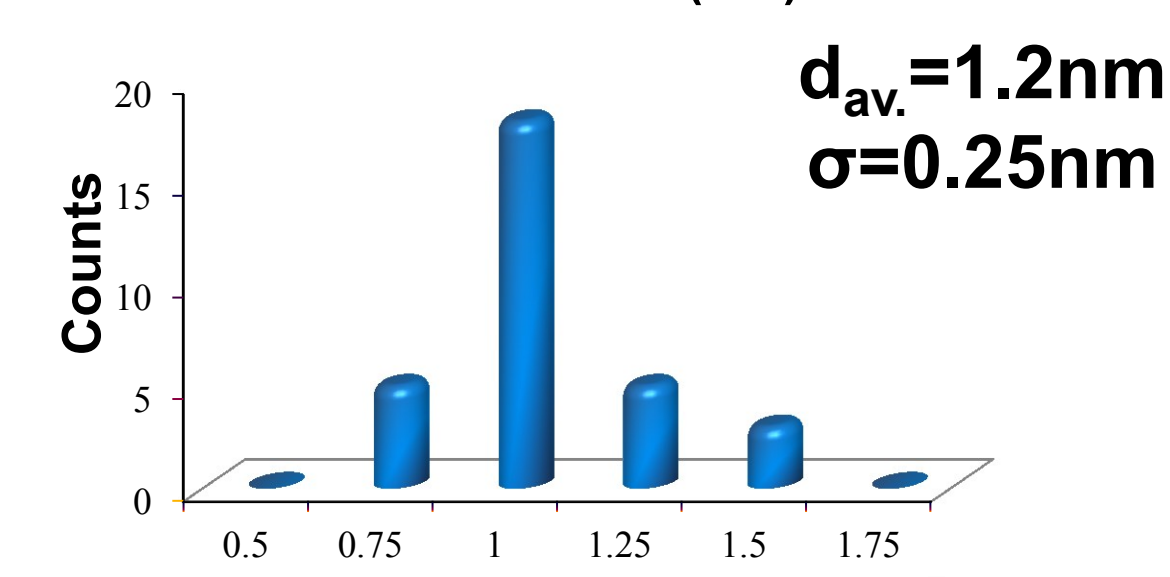


Colored high resolution SEM micrograph and its schematic representation. A SWCNT is grown by CVD from ethanol over a $2 \mu\text{m}$ deep trench from one patterned Co nanoparticles. It has a diameter of $1.2 \pm 0.25 \text{ nm}$ corresponding to the diameter of the Co nanoparticles.

- Growth temperature: 800°C
- Carbon source: Ethanol

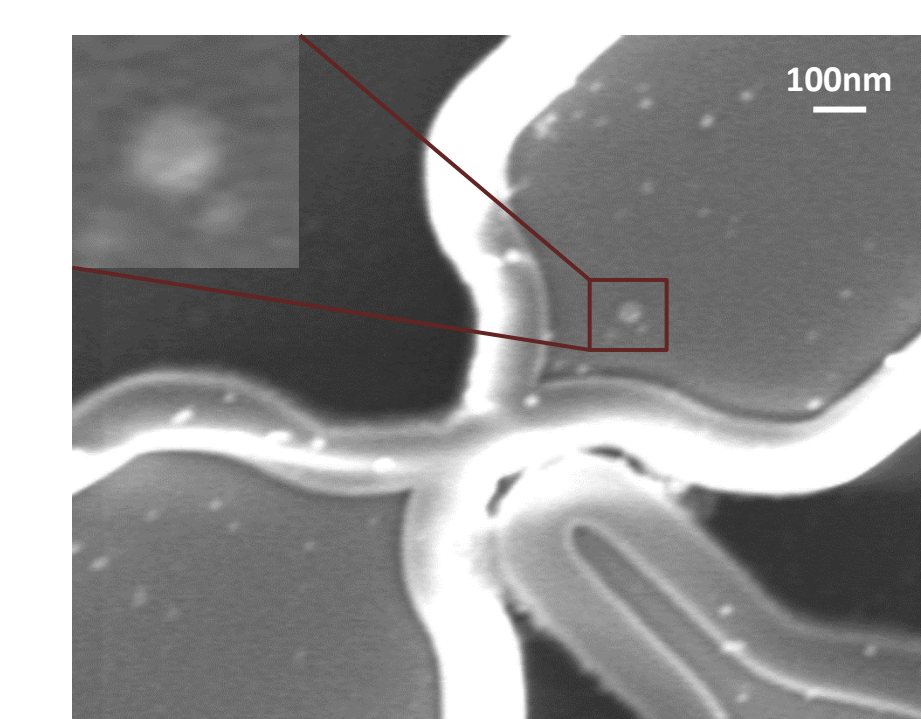
AFM analysis

CNT diameter (nm)



- 100% of the particles yield a SWCNT

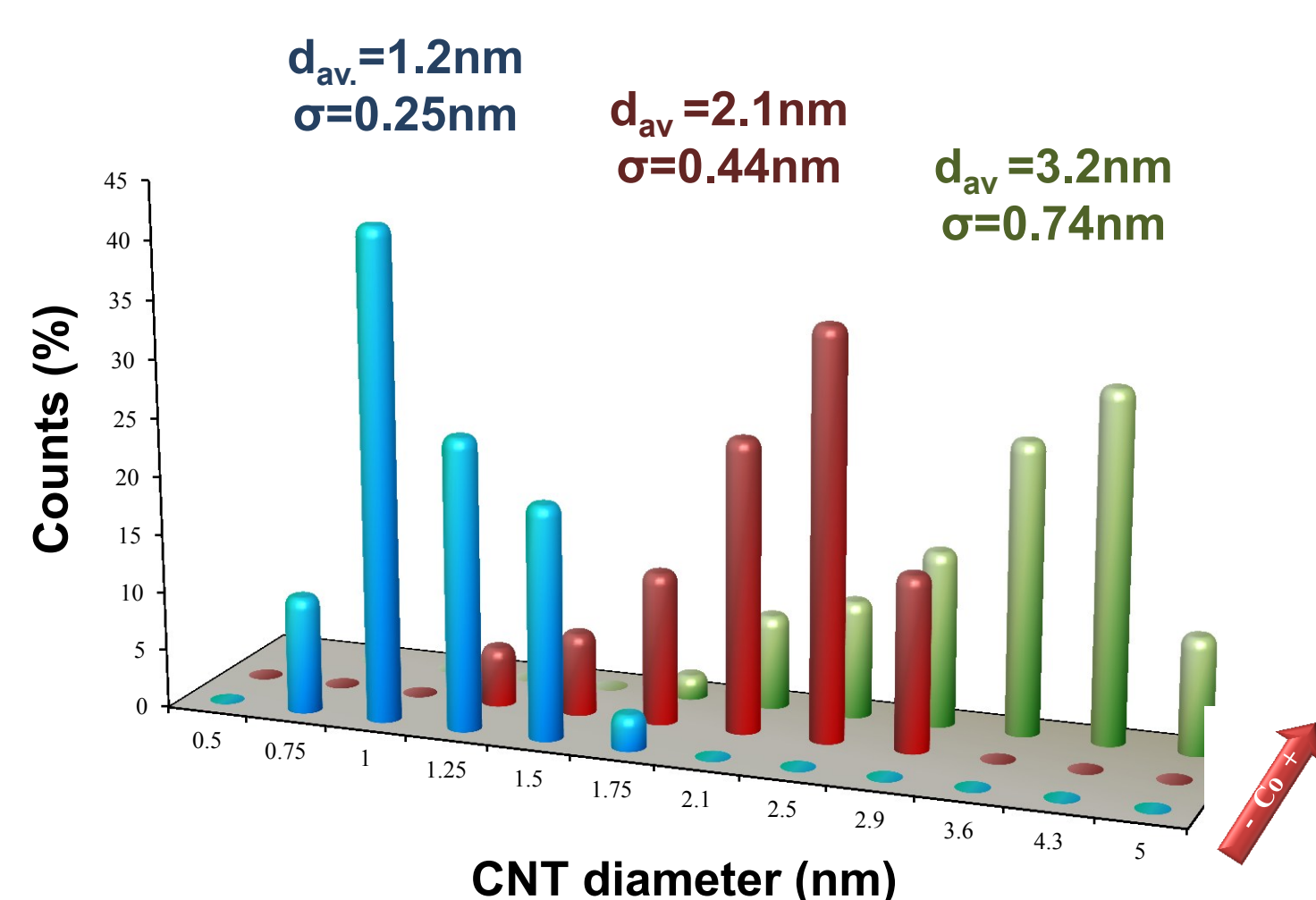
Integration into NEMS process flow



SEM micrograph of a NEMS with patterned catalyst particle.

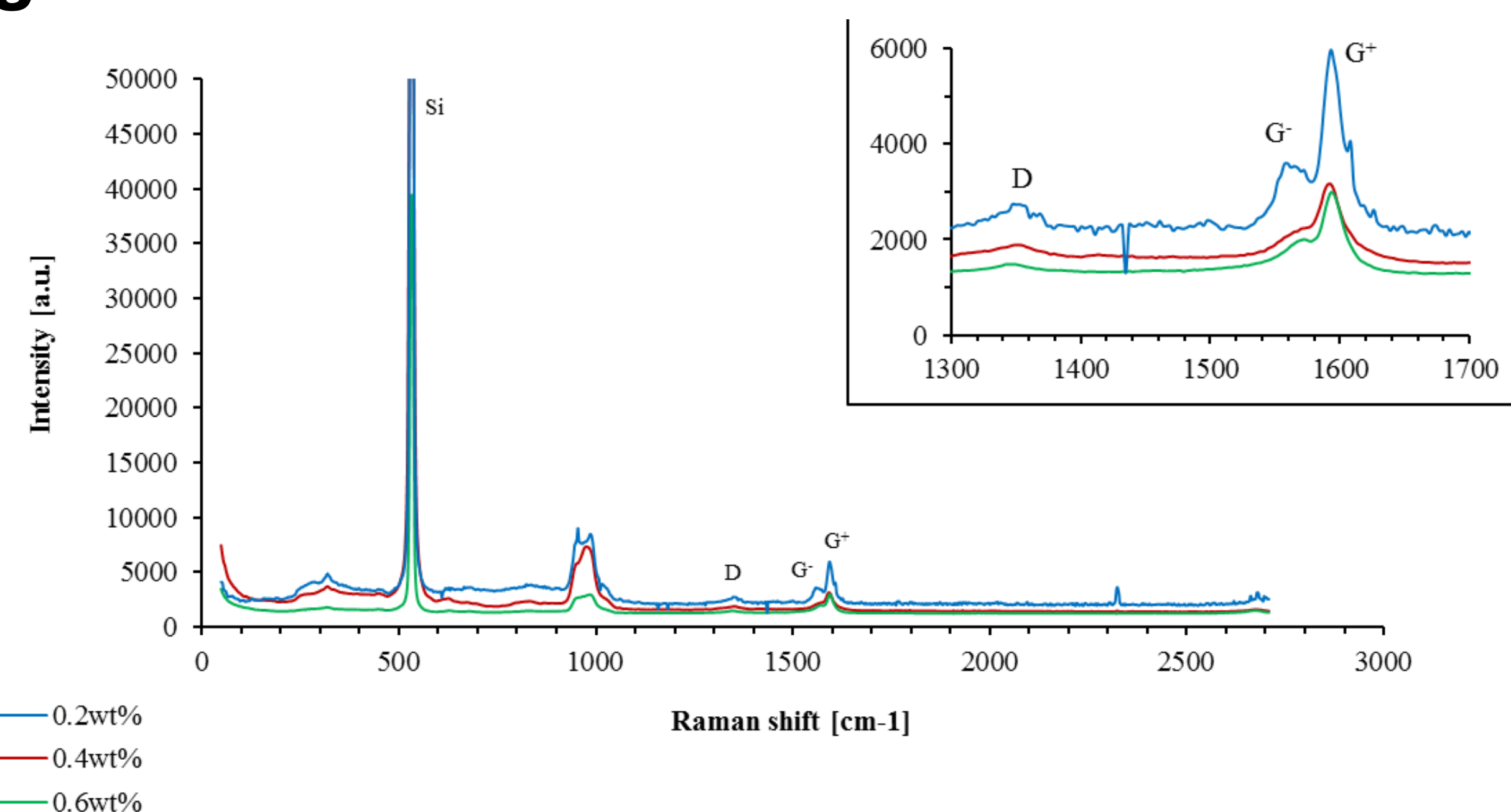
- 1 Cobalt nanoparticle (NP) in a 250 nm^2 area

Characterization of the Growth of Single Walled Carbon Nanotubes



Diameter distribution of the grown SWCNTs, established by AFM analysis, for different Co concentrations in the calix[6]arene resist.

- For a defined patterned area, the increase of the Co concentration in the resist leads to the growth of bundles of 1.2 nm SWCNTs.



Raman spectra of the grown SWCNTs for three concentrations of Co in the resist. Nanotube structure contains limited defects. Despite the increase of the metal concentration, their average diameter remains in the 1.2 nm range.

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